IN THE CLAIMS:

Claims 1-3, and 5-25 have been amended. All of the pending claims 1 through 25 are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as amended.

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1. (Currently Amended) A method for testing a plurality of semiconductor components, comprising:

forming a plurality of dice on a semiconductor wafer, said the plurality of dice each including at least one die contact; and

forming at least one wafer-level redistribution circuit on each of-said the plurality of dice for interconnection with others of-said the plurality of dice,-said the at least one wafer-level redistribution circuit including a redistribution-eireuit circuit, and a bus conductor traversing each of-said the plurality of dice for electrically coupling with at least another one of-said the plurality of dice and at least one conductor for coupling-said the redistribution circuit to-said the bus conductor.

- 2. (Currently Amended) The method, as recited in claim 1, further comprising forming an outer passivation layer on an exposed face of said the semiconductor wafer covering said the redistribution circuit and said the bus conductor.
- 3. (Currently Amended) The method, as recited in claim 2, further comprising probing each of said the plurality of dice to determine functional and nonfunctional dice.
- 4. (Original) The method, as recited in claim 3, further comprising storing location information on nonfunctional dice.
- 5. (Currently Amended) The method, as recited in claim 4, further comprising isolating at least one die contact on each of said the nonfunctional dice.

- 6. (Currently Amended) The method, as recited in claim 5, wherein said isolating includes removing a portion of said the outer passivation layer over said the at least one of said the redistribution circuit and said the bus connector conductor to form an open circuit between said the at least one die contact and said the bus conductor on said the nonfunctional dice.
- 7. (Currently Amended) The method, as recited in claim 5, wherein said isolating includes ablating of at least a portion of said the at least one wafer-level redistribution circuit and said the outer passivation layer.
- 8. (Currently Amended) The method, as recited in claim 5, wherein said-isolating includes etching of at least a portion of said the at least one wafer-level redistribution circuit and said the outer passivation layer.
- 9. (Currently Amended) A method for manufacturing wafer-level testable dice, comprising:
- forming a plurality of dice on a semiconductor wafer, said the plurality of dice each including at least one die contact; and
- forming at least one wafer-level redistribution circuit on each of-said the plurality of dice for interconnection with others of-said the plurality of dice, said the at least one wafer-level redistribution circuit including a redistribution circuit, and a bus conductor traversing each of-said the plurality of dice for electrically coupling with at least another one of-said the plurality of dice and at least one other bus conductor for coupling said the redistribution circuit to-said the bus conductor.
- 10. (Currently Amended) The method, as recited in claim 9, further comprising isolating at least one of said the at least one die contact on nonfunctional dice of said the plurality of dice on said the semiconductor wafer.

- 11. (Currently Amended) The method, as recited in claim 9, further comprising probing each of said the plurality of dice to determine functional and nonfunctional dice of said the plurality of dice.
- 12. (Currently Amended) A method for fabricating a wafer-level testable semiconductor component, comprising:
- forming a plurality of dice on a semiconductor wafer, said the plurality of dice each including at least one die contact;
- forming at least one wafer-level redistribution circuit on each of-said the plurality of dice for interconnection with others of-said the plurality of dice, said the at least one wafer-level redistribution circuit including a redistribution circuit, and a bus conductor traversing each of said the plurality of dice for electrically coupling with at least another one of-said the plurality of dice and at least one other bus conductor for coupling said the redistribution circuit to-said the bus conductor;

isolating said the at least one die contact on each nonfunctional die of said the plurality of dice; testing functional dice of said the plurality of dice while integral with said the semiconductor wafer; and

singulating one of said the functional dice of said the plurality of dice from said the semiconductor component.

- 13. (Currently Amended) The method, as recited in claim 12, wherein said isolating further comprises probing each of said the plurality of dice to determine said the functional dice and said the nonfunctional dice of said the plurality of dice.
- 14. (Currently Amended) The method, as recited in claim 12, further comprising burning-in-said the semiconductor component while-said the semiconductor component is integral with-said the semiconductor wafer.

- 15. (Currently Amended) A method for retrofitting an existing wafer layout for wafer-level testing, comprising:
- on a semiconductor wafer including a plurality of dice with each die including at least one die contact, forming at least one wafer-level redistribution circuit on each of said the plurality of dice for interconnection with others of said the plurality of dice, said the at least one wafer-level redistribution circuit including a redistribution circuit for coupling said the at least one die contact to a respective bumped contact, a bus conductor traversing at least a portion of each of said the plurality of dice for electrically coupling with at least another one of said the plurality of dice, said the at least one other bus conductor for coupling said the redistribution circuit to said the bus conductor; and

isolating at least one die contact on each nonfunctional die of-said the plurality of dice.

- 16. (Currently Amended) The method, as recited in claim 15, wherein said-forming further comprises forming an outer passivation layer over-said the redistribution circuit and-said the bus conductor.
- 17. (Currently Amended) The method, as recited in claim 15, wherein said-isolating further comprises probing each of said the plurality of dice to determine functional dice and said the nonfunctional dice of said the plurality of dice.
- 18. (Currently Amended) The method, as recited in claim 16, wherein said isolating includes removing a portion of said the outer passivation layer over said the at least one of said wafer-level redistribution circuit and forming an open circuit between said the at least one die contact and said the bus conductor on said the nonfunctional dice.
- 19. (Currently Amended) The method, as recited in claim 18, wherein said-isolating includes ablating of at least a portion of said the at least one wafer-level redistribution circuit and said the outer passivation layer.

- 20. (Currently Amended) The method, as recited in claim 18, wherein said-isolating includes etching of at least a portion of-said the at least one wafer-level redistribution circuit and said the outer passivation layer.
- 21. (Currently Amended) A method for isolating nonfunctional dice from a wafer-level testing configuration, comprising:

forming at least one wafer-level redistribution circuit on each of said a plurality of dice for interconnection with others of said the plurality of dice, said the at least one wafer-level redistribution circuit including a redistribution circuit for coupling at least one die contact to a respective bumped contact, a bus conductor traversing each of said the plurality of dice for electrically coupling with at least another one of said the plurality of dice and at least one other bus conductor for coupling said the redistribution circuit to said the bus conductor; and

isolating at the at least one die contact on each nonfunctional die of said the plurality of dice.

- 22. (Currently Amended) The method, as recited in claim 21, further comprising forming an outer passivation layer over-said the at least one redistribution circuit and said the at least one other bus conductor.
- 23. (Currently Amended) The method, as recited in claim 22, wherein-said the outer passivation layer is selectively removable over at least a portion of one of-said the at least one redistribution circuit and at least one other bus conductor for forming an electrical open circuit between-said the at least one die contact and-said the at least one other bus conductor when a die of-said the plurality of dice is determined to be defective.

- 24. (Currently Amended) The method, as recited in claim 23, wherein said isolating includes etching said the at least one redistribution circuit to form said the electrical open circuit.
- 25. (Currently Amended) The method, as recited in claim 23, wherein said-isolating includes ablating said the at least one redistribution circuit by a laser to form-said the electrical open circuit.